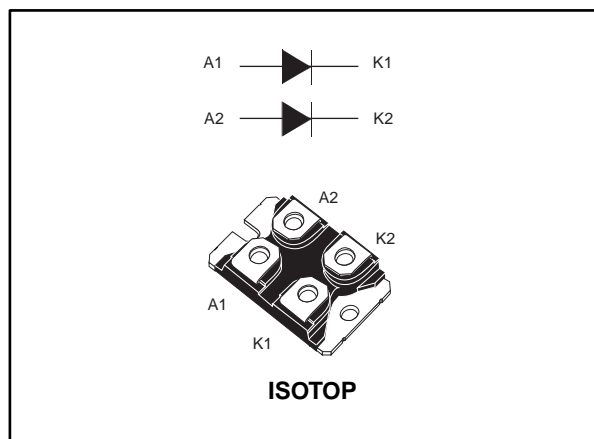


High voltage power Schottky rectifier

Datasheet - production data



Description

This high voltage Schottky rectifier is suited for high frequency switch mode power supplies.

Packaged in ISOTOP, this device is intended for use in the secondary rectification of applications.

Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	2 x 100 A
V_{RRM}	170 V
T_j (max.)	150 °C
V_F (max.)	0.63 V

Features

- Negligible switching losses
- Avalanche rated
- Low leakage current
- Good trade-off between leakage current and forward voltage drop
- Insulated package ISOTOP:
 - Insulated voltage: 2500 V_{RMS}
 - Capacitance: 45 pF

1 Characteristics

Table 2: Absolute ratings (limiting values, per diode at T_{amb} = 25 °C, unless otherwise specified)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			170	V
I _{F(RMS)}	Forward rms current			200	A
I _{F(AV)}	Average forward current, δ = 0.5	T _C = 105 °C	Per diode	100	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal		700	A
P _{ARM}	Repetitive peak avalanche power	t _p = 10 μs T _j = 125 °C		7400	W
T _{stg}	Storage temperature range			-55 to +150	°C
T _j	Maximum operating junction temperature ⁽¹⁾			150	°C

Notes:

⁽¹⁾(dP_{tot}/dT_j) < (1/R_{th(j-a)}) condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Thermal parameters

Symbol	Parameter		Maximum values	Unit
R _{th(j-c)}	Junction to case	Per diode	0.52	°C/W
		Total	0.31	
R _{th(c)}	Coupling thermal resistance		0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P_{(\text{diode1})} \times R_{th(j-c)} (\text{per diode}) + P_{(\text{diode2})} \times R_{th(c)}$$

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}	-		200	μA
		T _j = 125 °C		-	30	100	mA
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 100 A	-		0.85	V
		T _j = 150 °C		-	0.63	0.68	
		T _j = 25 °C	I _F = 200 A	-		0.975	
		T _j = 150 °C		-	0.78	0.86	

Notes:

⁽¹⁾Pulse test: t_p = 5 ms, δ < 2%

⁽²⁾Pulse test: t_p = 380 μs, δ < 2%

To evaluate the maximum conduction losses, use the following equation:

$$P = 0.5 \times I_{F(AV)} + 0.0018 \times I_{F(RMS)}^2$$



1.1 Characteristics (curves)

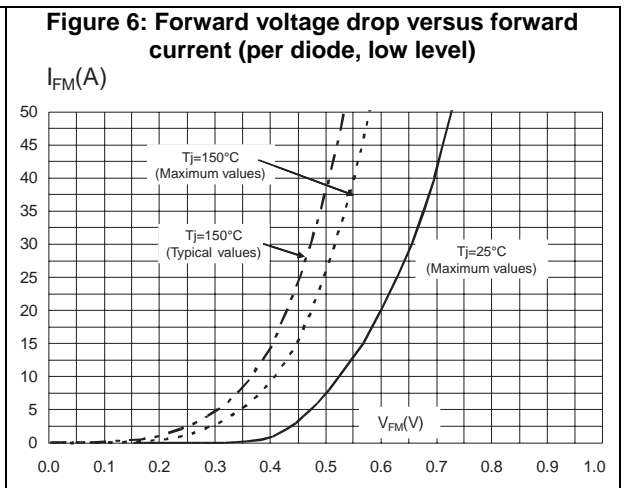
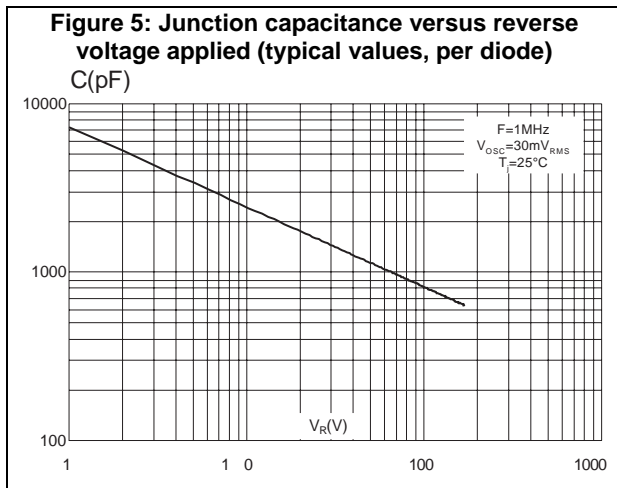
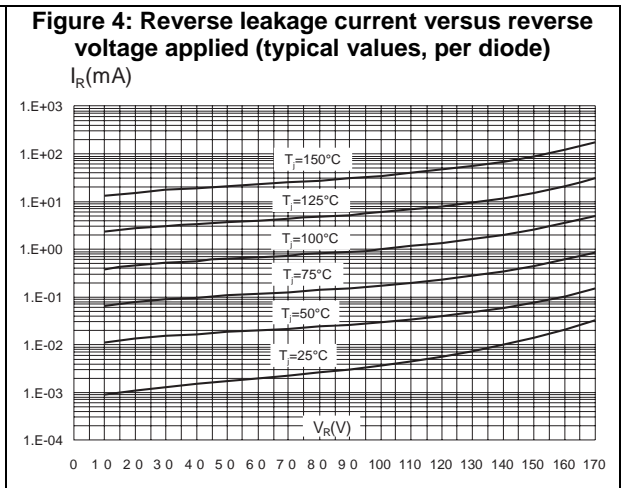
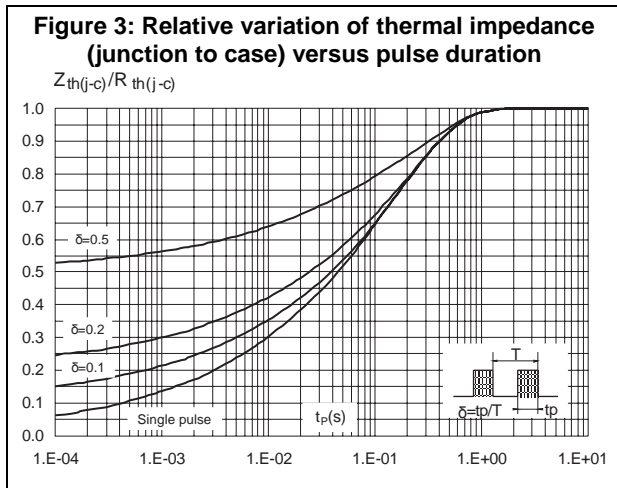
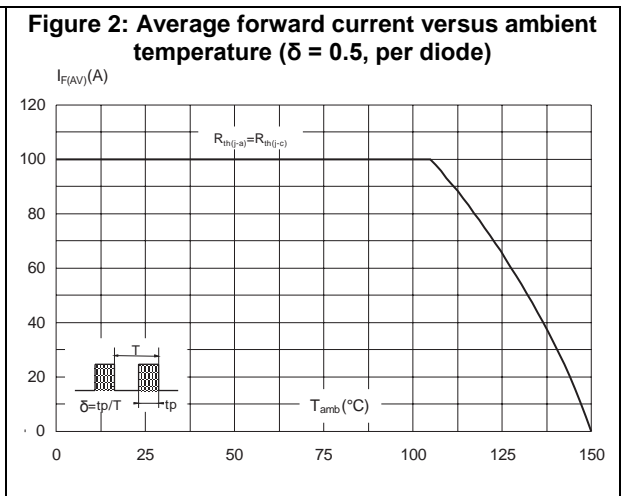
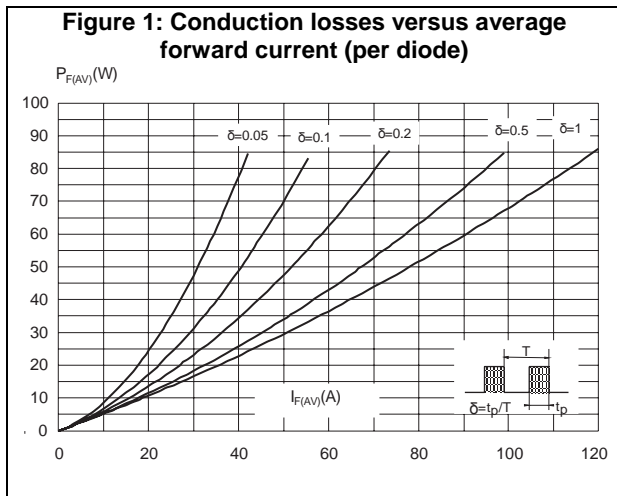


Figure 7: Forward voltage drop versus forward current (per diode, high level)

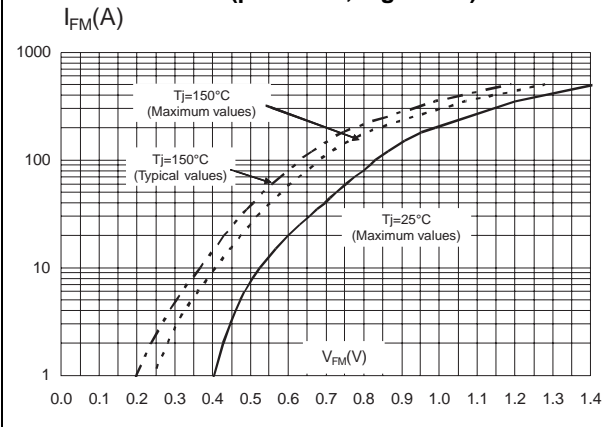
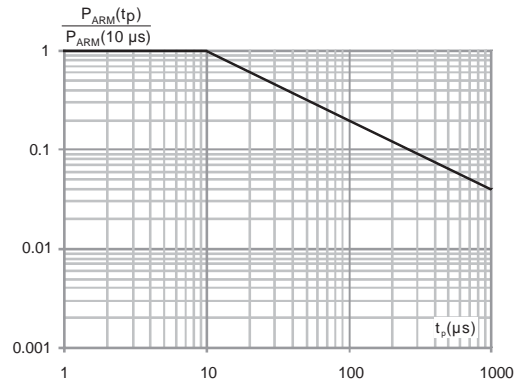


Figure 8: Normalized avalanche power derating versus pulse duration



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N·m
- Maximum torque value: 1.5 N·m

STMicroelectronics strongly recommends the use of the screws delivered with this product.

The use of any other screws is entirely at the user's own risk and will invalidate the warranty.

2.1 ISOTOP package information

Figure 9: ISOTOP package outline

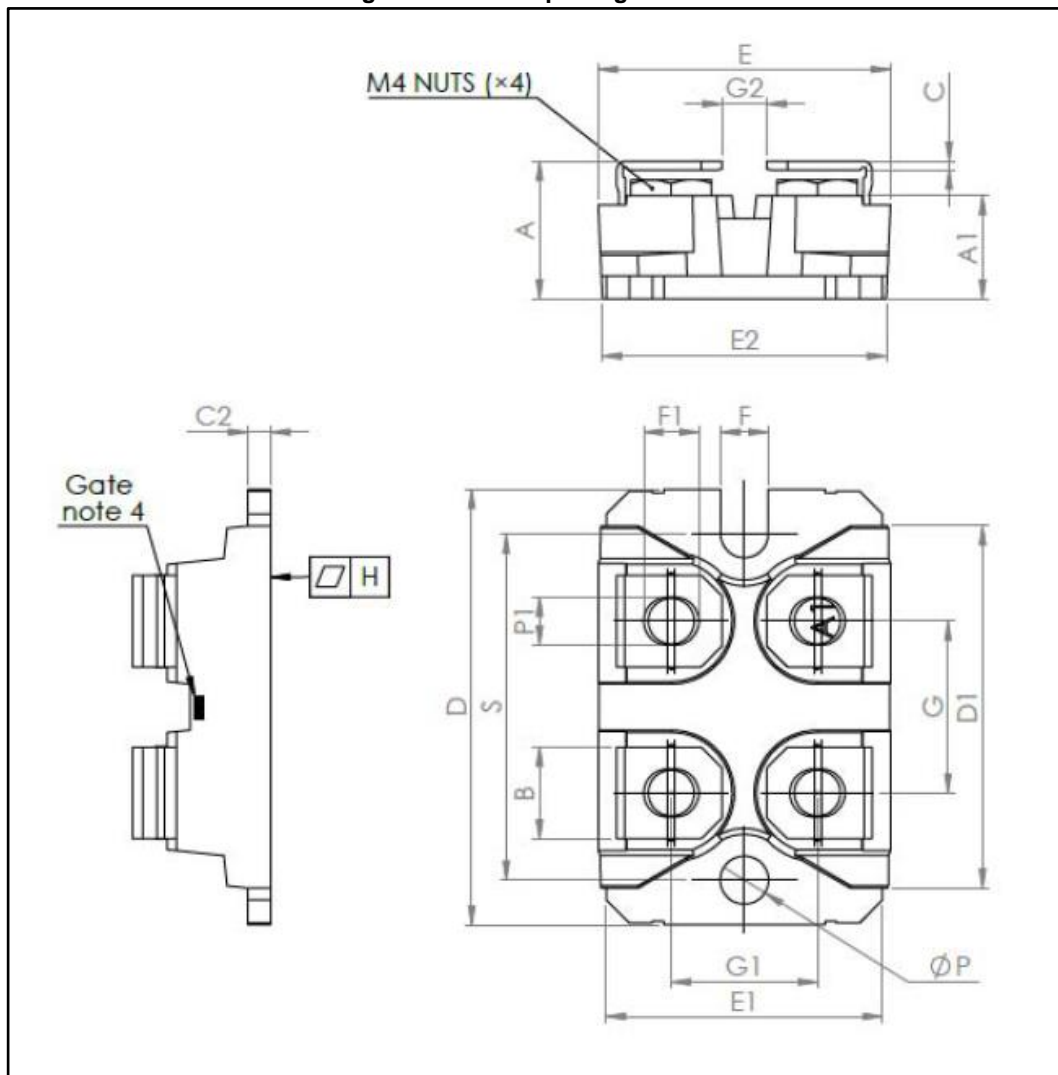


Table 5: ISOTOP package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.80	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80		0.976	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5	0.181	0.197
H	-0.05	0.1	-0.002	0.004
Diam P	4	4.30	0.157	0.169
P1	4	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

3 Ordering information

Table 6: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS200170TV1	STPS200170TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Table 7: Document revision history

Date	Revision	Changes
14-Nov-2005	1	First issue.
09-Sep-2011	2	Updated V_F max at $T_j = 25\text{ °C}$ and $I_F = 100\text{ A}$ to 0.85 V.
12-Feb-2018	3	Updated Table 2: "Absolute ratings (limiting values, per diode at $T_{amb} = 25\text{ °C}$, unless otherwise specified)" and the new PARM curve at 10 μs .

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics – All rights reserved